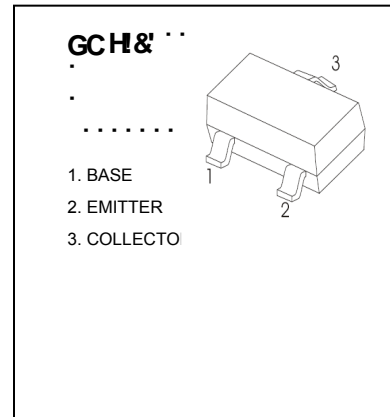


.....67, %± TRANSISTOR (NPN)



: 95HI F9G'

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC807 (PNP)

A5L-AI A'F5HB; G'fh1&) °C'i b'Ygg'cH Yfk JgY'bcHXL'

Gna Vc''	DUFUa YHf'	JUi Y'	I b]h
J76c'	Collector-Base Voltage	50	V
J79c'	Collector-Emitter Voltage	45	V
J96c'	Emitter-Base Voltage	5	V
7'	Collector Current -Continuous	0.5	A
D7'	Collector Power Dissipation	0.3	W
H^	Junction Temperature	150	°C
H _{glt} '	Storage Temperature	-55-150	°C

'9 @7 HF 7 5 @7 <5 F57 H9F -GH7 G'fh1&) °C'i b'Ygg'cH Yfk JgY'gdYWZ'YXL'

..... DUFUa YHf'	Gna Vc''	'HYgh VtbX]hcbg'	Ain	Typ'	Aax	Unit
7c''YWcf!VUgY'VfYU_Xck b'j'c'HU] Y'	V _{CB0}	I _C = 10μA, I _E =0	50			V
7c''YWcf!Ya]Hf'VfYU_Xck b'j'c'HU] Y'	V _{CE0}	I _C = 10mA, I _B =0	45			V
9a]Hf'!VUgY'VfYU_Xck b'j'c'HU] Y'	V _{EBO}	I _E = 1μA, I _C =0	5			V
7c''YWcf'W HcZZW ffYbh	I _{CB0}	V _{CB} = 45 V, I _E =0			0.1	μA
9a]Hf'W HcZZW ffYbh	I _{EBO}	V _{EB} = 4V, I _C =0			0.1	μA
87'W ffYbh[U]b.....	h _{FE(1)}	V _{CE} = 1V, I _C = 100mA	100		600	
	h _{FE(2)}	V _{CE} = 1V, I _C = 500mA	40			
7c''YWcf!Ya]Hf'gUhfU]cb'j'c'HU] Y'	V _{CE(sat)}	I _C = 500mA, I _B = 50mA			0.7	V
6UgY!Ya]Hf'gUhfU]cb'j'c'HU] Y'	V _{BE(sat)}	I _C = 500mA, I _B = 50mA			1.2	V
6UgY!Ya]Hf'j'c'HU] Y'	V _{BE}	V _{CE} = 1 V, I _C = 500mA			1.2	V
7c''YWyf'WUdUW]UbW'	C _{ob}	V _{CB} =10V, f=1MHz		10		pF
HfUbg]hcb'Z'YeI YbWni	f _T	V _{CE} = 5 V, I _C = 10mA f=100MHz	100			MHz

7 @ GG= 7 5 HCB'C: 'h_{FE}'%

FUb_'	67, %±!%'	67, %±!&)'	67, %±!('\$'
FUb[Y'	%'\$!&)' \$'	%'\$!('\$\$'	&)'\$!*\$\$\$'
AUf_]b['	* 5'	* 6'	* 7'

